

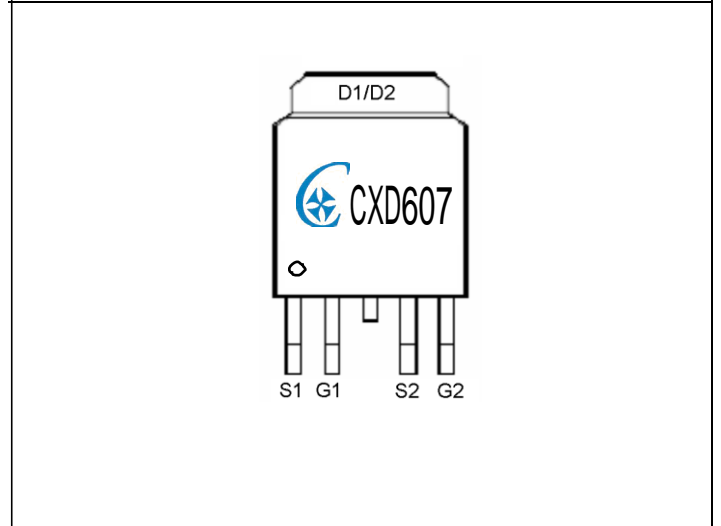
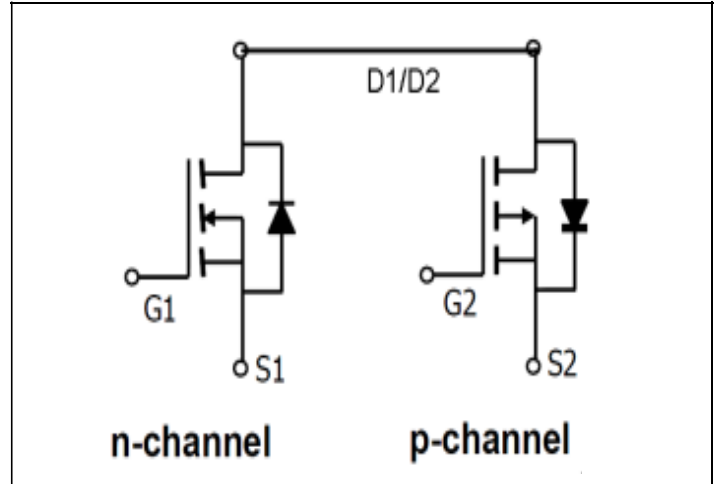


## N+P-channel Enhancement Mode Mosfet

## CXD607

### DESCRIPTION

The CXD607 is the highest performance trench N-Ch and P-Ch MOSFETs With extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.



### GENERAL FEATURES

#### Features

n-channel	p-channel
$V_{DS} (V) = 30V$	$-30V$
$I_D = 12A (V_{GS}=10V)$	$-12A (V_{GS} = -10V)$
$R_{DS(ON)} < 29 m\Omega (V_{GS}=10V)$	$R_{DS(ON)} < 55 m\Omega (V_{GS} = -10V)$
$< 40 m\Omega (V_{GS}=4.5V)$	$< 68 m\Omega (V_{GS} = -4.5V)$

**100% UIS Tested!**

### Application

- ◆ Drivers: Relays, lamps, Memories.
- ◆ Battery operated systems.
- ◆ CCFL Back-light Inverter
- **Absolute Maximum Ratings** ( $T_A=25^\circ C$  unless otherwise noted)

Symbol	Parameter	Rating		Unit
		N-Ch	P-Ch	
VDSS	Drain-Source Voltage	30	-30	V
VGSS	Gate-Source Voltage	$\pm 20$	$\pm 20$	
ID	Continuous Drain Current ,(VGS=10V)	12	-12	A
IDM	Drain Current (Pulse)	40	-40	A
TJ	Maximum Junction Temperature	-55 TO 175		°C
TSTG	Storage Temperature Range	-55 TO 175		
PD	Maximum Power Dissipation (Ta=25°C)	25	25	W